

isc Silicon NPN Power Transistor

2SC3632

DESCRIPTION

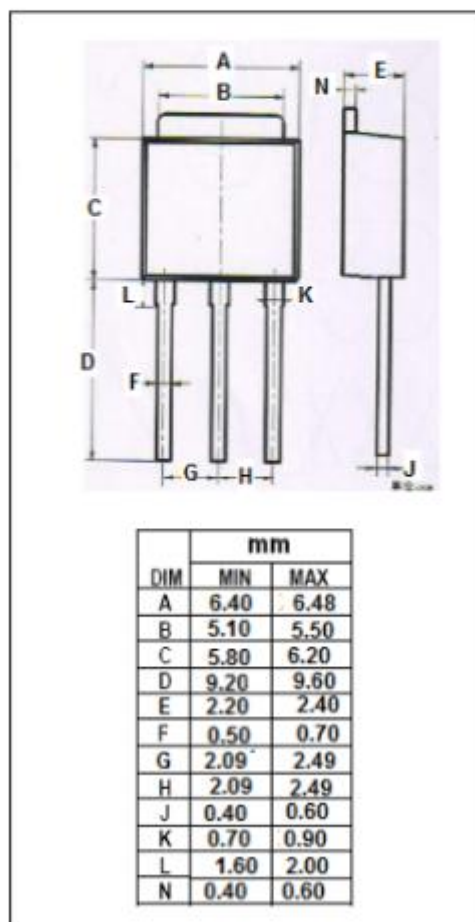
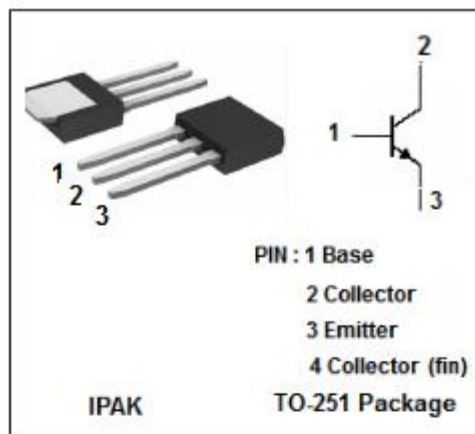
- High Collector-Emitter Voltage
- Low collector saturation voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High voltage switching.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	600	V
V _{CEO}	Collector-Emitter Voltage	600	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current-Continuous	1	A
P _C	Collector Power Dissipation	2.0	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SC3632****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$ ^{NOTE}	Collector-Emitter Saturation Voltage	$I_C=400\text{mA}; I_B=80\text{mA}$			1	V
$V_{BE(sat)}$ ^{NOTE}	Base-Emitter Saturation Voltage	$I_C=400\text{mA}; I_B=80\text{mA}$			1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=600\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			10	μA
h_{FE-1} ^{NOTE}	DC Current Gain	$I_C=100\text{mA}; V_{CE}=5\text{V}$	30		120	
h_{FE-2} ^{NOTE}	DC Current Gain	$I_C=500\text{mA}; V_{CE}=2\text{V}$	5			

NOTE: Pulse test $PW \leq 350\mu\text{s}$, duty cycle $\leq 2\%$ ◆ **h_{FE-1} Classifications**

M	L	K
30-60	40-80	60-120